

Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	09/838,316
		Filing Date	4/20/01
		First Named Inventor	Lu
		Group Art Unit	Unknown #13
		Examiner Name	Unassigned <i>Sark Chen</i>
Sheet 1	of 1	Attorney Docket Number	95-153



OTHER PRIOR ART — NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
~		J. STOEMENOS et al, "Dislocation formations related with high oxygen dose implantation on silicon." J. App1 Phys., 69(1991), p.793.	
~		D. HILL et al, "The reduction of dislocations in oxygen implanted silicon on insulator layers by sequential implantation and annealing." J. App1 Phys., 63(1998), p. 4933.	
~		S. NAKASHIMA et al, "Investigations on high temperatures thermal oxidataion press at top and bottom interfaces of top silicon of SIMOX wafers." J. Electrochem. Soc., p. 244, 1996.	
~		L. NESBIT et al, "Microstructure of silicon implanted with high dose of nitrogen and oxygen." J. Electrochem. Soc., 133(1986), p.1186.	

Examiner Signature	<i>Sark Chen</i>	Date Considered	11/26/02
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here is English language Translation is attached.